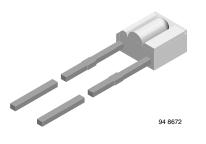
TSSS2600

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Vishay Semiconductors

Infrared Emitting Diode, 950 nm, GaAs



DESCRIPTION

TSSS2600 is an infrared, 950 nm emitting diode in GaAs technology, molded in a miniature, clear plastic package with side view lens.

FEATURES

- · Package type: leaded
- Package form: side view
- Dimensions (L x W x H in mm): 3.6 x 2.2 x 5
- Peak wavelength: $\lambda_p = 950 \text{ nm}$
- High reliability
- · High radiant power
- · High radiant intensity
- Angle of half intensity: $\phi = \pm 25^{\circ}$, horizontal
- · Low forward voltage
- Suitable for high pulse current operation
- · Good spectral matching with Si photodetectors
- · Package matched with detector TEST2600
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

 Infrared source in miniature light barriers or reflective sensor systems with short transmission distances and low forward voltage requirements. Matching with silicon PIN photodiodes or phototransistors (e.g. TEST2600)

PRODUCT SUMMARY

COMPONENT	I _e (mW/sr)	φ (°)	λ _p (nm)	t _r (ns)
TSSS2600	2.6	± 25	950	800

Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	DE PACKAGING		PACKAGE FORM	
TSSS2600	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	Side view	

Note

• MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	2.0	А	
Power dissipation		Pv	170	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \leq 5 \mbox{ s}, 2 \mbox{ mm}$ from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	Leads not soldered	R _{thJA}	450	K/W	

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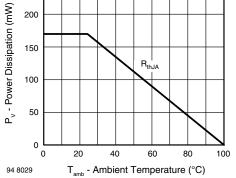


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

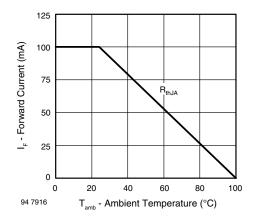


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTIC	S (T _{amb} = 25 °C, unless othe	rwise specifie	ed)		-	-
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F		1.25	1.6	V
	I _F = 1.5 A, t _p = 100 μs	V _F		2.2		V
Temperature coefficient of V _F	I _F = 100 mA	TK _{VF}		- 1.3		mV/K
Reverse current	V _R = 5 V	I _R			100	μA
Junction capacitance	$V_{R} = 0 V, f = 1 MHz, E = 0$	Cj		30		pF
Radiant intensity	I _F = 100 mA, t _p = 20 ms	l _e	1	2.6	3	mW/sr
	I _F = 1.5 A, t _p = 100 μs	l _e		25		mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	\$e		20		mW
Temperature coefficient of ϕ_{e}	I _F = 100 mA	ΤKφ _e		- 0.8		%/K
Angle of half intensity	horizontal	φ1		± 25		0
	vertical	φ ₂		± 60		0
Peak wavelength	I _F = 100 mA	λρ		950		nm
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm
Temperature coefficient of λ_p	I _F = 100 mA	ΤΚλρ		0.2		nm/K
Rise time	I _F = 100 mA	t _r		800		ns
	I _F = 1.5 A	t _r		400		ns
Fall time	I _F = 100 mA	t _f		800		ns
	I _F = 1.5 A	t _f		400		ns
Virtual source diameter		d		2		mm



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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

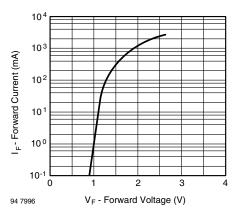


Fig. 3 - Pulse Forward Current vs. Forward Voltage

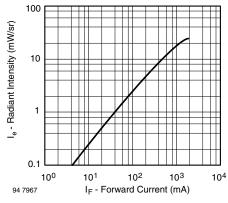


Fig. 4 - Radiant Intensity vs. Forward Current

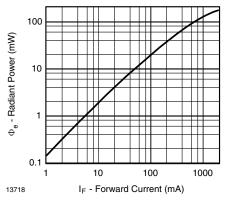


Fig. 5 - Radiant Power vs. Forward Current

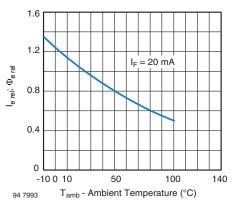


Fig. 6 - Relative Radiant Intensity/Power vs. Ambient Temperature

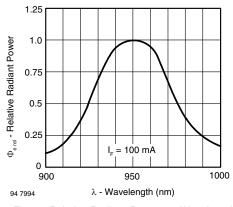


Fig. 7 - Relative Radiant Power vs. Wavelength

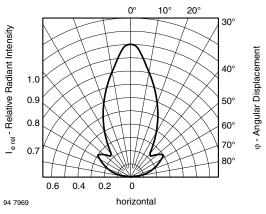


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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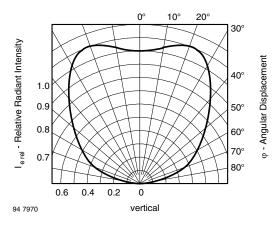
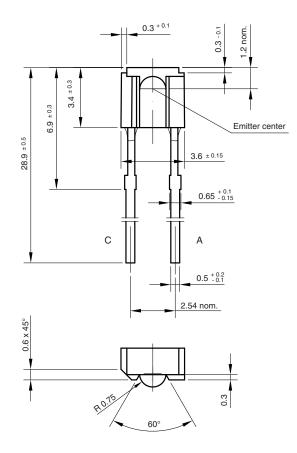
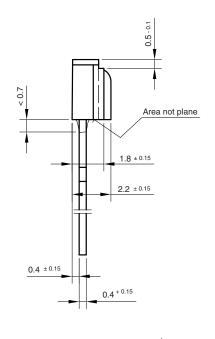


Fig. 1 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters







according to DIN specifications

Drawing-No.: 6.544-5241.01-4 Issue: 3; 18.04.96 95 11488

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